# **74AHCV245A**

# Octal bus transceiver; 3-state Rev. 1 — 10 June 2016

**Product data sheet** 

#### **General description** 1.

The 74AHCV245A is an 8-bit transceiver with 3-state outputs and Schmitt trigger inputs. The device features an output enable (OE) and send/receive (DIR) for direction control. A HIGH on OE causes the outputs to assume a high-impedance OFF-state.

Inputs are overvoltage tolerant. This feature allows the use of these devices as translators in mixed voltage environments.

The data (An, Bn) and control (OE and DIR) inputs include Schmitt trigger inputs. These inputs can of transform slowly changing input signals into sharply defined, jitter-free output signals.

This device is ideal for driving bus lines or buffer memory address registers. It features inputs and outputs on opposite sides of the package to facilitate printed circuit board layout.

This device is fully specified for partial Power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

#### Features and benefits 2.

- Wide supply voltage range from 1.8 V to 5.5 V
- Typical t<sub>pd</sub> of 3.2 ns at 5 V
- Typical  $V_{OL(p)}$  < 0.8 V at  $V_{CC}$  = 3.3 V,  $T_{amb}$  = 25 °C
- Typical  $V_{OH(v)} > 2.3 \text{ V}$  at  $V_{CC} = 3.3 \text{ V}$ ,  $T_{amb} = 25 ^{\circ}\text{C}$
- Supports mixed-mode voltage operation on all ports
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Latch-up performance exceeds 250 mA per JESD 78 Class II
- ESD protection:
  - ◆ HBM ANSI/ESDA/JEDEC JS-001 Class 2 exceeds 3 kV
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 2 kV
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

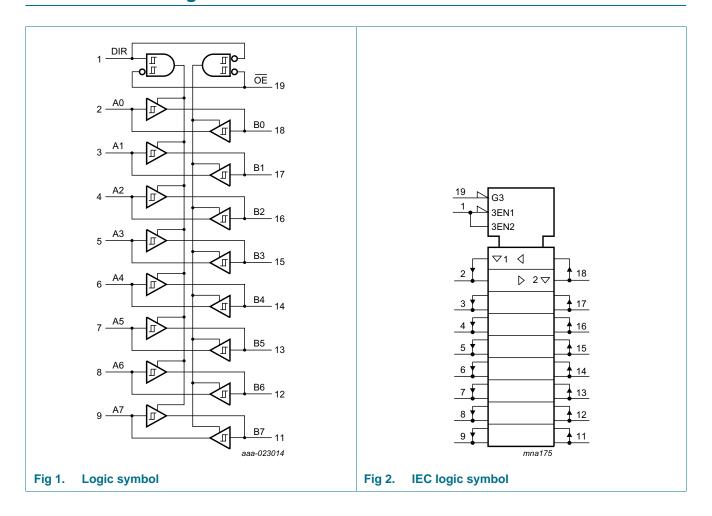


# 3. Ordering information

Table 1. Ordering information

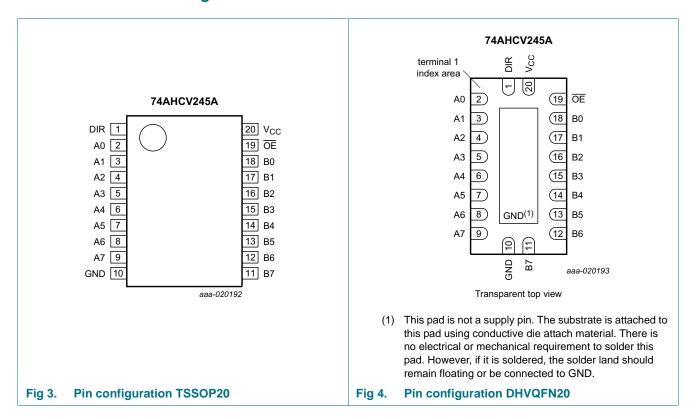
Type number	Package						
	Temperature range	Name	Description	Version			
74AHCV245APW	–40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1			
74AHCV245ABQ	–40 °C to +125 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85$ mm	SOT764-1			

## 4. Functional diagram



## 5. Pinning information

#### 5.1 Pinning



## 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DIR	1	direction control
A0 to A7	2, 3, 4, 5, 6, 7, 8, 9	data input/output
GND	10	ground (0 V)
B0 to B7	18, 17, 16, 15, 14, 13, 12, 11	data input/output
ŌĒ	19	output enable input (active LOW)
Vcc	20	supply voltage

## 6. Functional description

Table 3. Function table[1]

		Input/output			
OE	DIR	An	Bn		
L	L	A = B	input		
L	Н	input	B = A		
Н	X	Z	Z		

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
VI	input voltage	[1]	-0.5	+7.0	V
V <sub>O</sub> output voltage		active mode [2][3]	-0.5	V <sub>CC</sub> + 0.5	V
		power-down or 3-state mode [2]	-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
I <sub>O</sub>	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I <sub>CC</sub>	supply current		-	100	mA
I <sub>GND</sub>	ground current		-100	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	-	500	mW

<sup>[1]</sup> If the input current ratings are observed, the minimum input voltage ratings may be exceeded.

<sup>[2]</sup> If the output current ratings are observed, the output voltage ratings may be exceeded.

<sup>[3]</sup> This value is limited to 7.0 V maximum.

<sup>[4]</sup> For TSSOP20 package: above 100 °C, the value of  $P_{tot}$  derates linearly with 10 mW/K. For DHVQFN20 package: above 110 °C, the value of  $P_{tot}$  derates linearly with 12.5 mW/K.

## 8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		1.8	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	active mode	0	V <sub>CC</sub>	V
		power-down or 3-state mode	0	5.5	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.3 V to 2.7 V	-	50	ms/V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	20	ms/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1	ms/V

## 9. Static characteristics

#### Table 6. Static characteristics

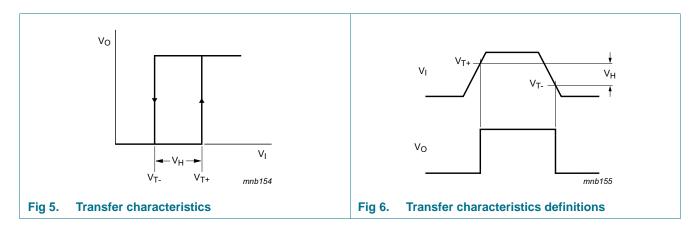
Voltages are referenced to GND (ground = 0 V).

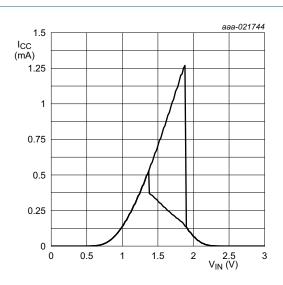
Symbol	Parameter	Conditions		25 °C		-40 °C to	+85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
$V_{T+}$	positive-going	V <sub>CC</sub> = 1.8 V	-	-	1.65	-	1.65	-	1.65	V
	threshold	V <sub>CC</sub> = 2.3 V	-	-	1.85	-	1.85	-	1.85	V
	voltage	V <sub>CC</sub> = 3.0 V	-	-	2.2	-	2.2	-	2.2	V
		V <sub>CC</sub> = 4.5 V	-	-	3.15	-	3.15	-	3.15	V
		V <sub>CC</sub> = 5.5 V	-	-	3.85	-	3.85	-	3.85	V
th	negative-going	V <sub>CC</sub> = 1.8 V	0.15	-	-	0.15	-	0.15	-	V
	threshold voltage	V <sub>CC</sub> = 2.3 V	0.45	-	-	0.45	-	0.45	-	V
		V <sub>CC</sub> = 3.0 V	0.9	-	-	0.9	-	0.9	-	V
		V <sub>CC</sub> = 4.5 V	1.35	-	-	1.35	-	1.35	-	V
		V <sub>CC</sub> = 5.5 V	1.65	-	-	1.65	-	1.65	-	V
$V_{H}$	hysteresis	V <sub>CC</sub> = 1.8 V	0.15	-	1.05	0.15	1.05	0.15	1.05	V
	voltage	V <sub>CC</sub> = 2.3 V	0.2	-	1.1	0.2	1.1	0.2	1.1	V
		V <sub>CC</sub> = 3.0 V	0.3	-	1.2	0.3	1.2	0.3	1.2	V
		V <sub>CC</sub> = 4.5 V	0.4	-	1.4	0.4	1.4	0.4	1.4	V
		V <sub>CC</sub> = 5.5 V	0.5	-	1.6	0.5	1.6	0.5	1.6	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{T+}$ or $V_{T-}$								V
	output voltage	$I_O = -50 \mu A; V_{CC} = 1.8 \text{ V}$	1.7	1.8	-	1.7	-	1.7	-	V
		$I_O = -50 \mu A; V_{CC} = 3.0 \text{ V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.48	-	V
		$I_{O} = -16 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.80	-	

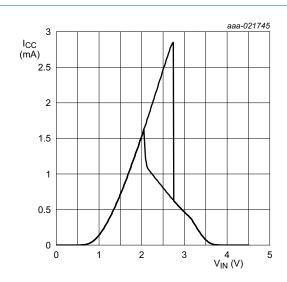
**Table 6. Static characteristics** ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
V <sub>OL</sub> LOW-level	$V_I = V_{T+}$ or $V_{T-}$									
	output voltage	$I_O = 50 \mu A; V_{CC} = 1.8 V$	-	0	0.1	-	0.1	-	0.1	V
	$I_O = 50 \mu A; V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V	
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
	$I_O = 8 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.44	V	
		$I_O = 16 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.44	-	0.55	-	0.55	V
I <sub>OZ</sub>	OFF-state output current	$V_{CC} = 5.5 \text{ V}; V_I = V_{IH} \text{ or } V_{IL};$ $V_O = \text{GND to } 5.5 \text{ V}$	-	-	±0.25	-	±2.5	-	±2.5	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O$ = GND to 5.5 V; $V_{CC}$ = 0 V	-	-	0.5	-	5	-	5	μΑ
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 0$ V to 5.5 V	-	-	±0.1	-	±1	-	±1	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	2	-	20	-	20	μΑ

## 9.1 Transfer characteristics waveforms

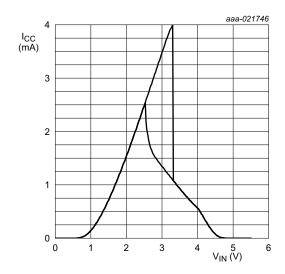






a.  $V_{CC} = 3.0 \text{ V}$ 





c.  $V_{CC} = 5.5 \text{ V}$ 

Fig 7. Typical transfer characteristics

**Product data sheet** 

# 10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V. For test circuit, see Figure 10.

Symbol	Parameter	Conditions		25 °C		-40 °C ⁴	to +85 °C	-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	1
t <sub>pd</sub>	propagation delay	An to Bn or Bn to An; see [2] Figure 8								
		V <sub>CC</sub> = 2.3 V to 2.7 V								
		C <sub>L</sub> = 15 pF	-	5.3	13	1	15	1	16.3	ns
		C <sub>L</sub> = 50 pF	-	7.3	15.9	1	18	1	19.4	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	4.1	8.4	1	10	1	10.9	ns
		C <sub>L</sub> = 50 pF	-	5.7	11.9	1	13.5	1	14.6	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	3.2	5.5	1	6.5	1	7	ns
		C <sub>L</sub> = 50 pF	-	4.5	7.5	1	8.5	1	9.3	ns
t <sub>en</sub> enable tim	enable time	OE to An or OE to Bn; see [2] Figure 9								
		V <sub>CC</sub> = 2.3 V to 2.7 V								
		C <sub>L</sub> = 15 pF	-	6.5	19.9	1	22	1	23	ns
		C <sub>L</sub> = 50 pF	-	8.6	22.7	1	26	1	27	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	4.9	13.2	1	15.5	1	16	ns
		C <sub>L</sub> = 50 pF	-	6.6	16.7	1	19	1	20	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	3.7	8.5	1	10	1	10.5	ns
		C <sub>L</sub> = 50 pF	-	5.1	10.6	1	12	1	12.5	ns
t <sub>dis</sub>	disable time	OE to An or OE to Bn; see [2] Figure 9								
		V <sub>CC</sub> = 2.3 V to 2.7 V								
		C <sub>L</sub> = 15 pF	-	7	15.1	1	16.7	1	17.8	ns
		C <sub>L</sub> = 50 pF	-	11.6	23.1	1	25	1	26	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	5.7	10.5	1	12.3	1	13.2	ns
		C <sub>L</sub> = 50 pF	-	9.1	15.8	1	18	1	19	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	4.5	6.9	1	8	1	8.5	ns
		C <sub>L</sub> = 50 pF	-	6.7	9.7	1	11	1	11.5	ns
t <sub>sk(o)</sub>	output skew	C <sub>L</sub> = 50 pF								
	time	V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	2	-	2	-	2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	1.5	-	1.5	-	1.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	1	-	1	-	1	ns

74AHCV245A

All information provided in this document is subject to legal disclaimers.

 Table 7.
 Dynamic characteristics ...continued

GND = 0 V. For test circuit, see Figure 10.

Symbol	Parameter	Conditions	25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit	
			Min	Typ[1]	Max	Min	Max	Min	Max	
Cı	input capacitance	$V_I = V_{CC}$ or GND; $V_{CC} = 3.3 \text{ V}$	-	2	6	-	6	-	6	pF
C <sub>I/O</sub>	input/output capacitance	$V_O = V_{CC}$ or GND; $V_{CC} = 3.3 \text{ V}$	-	5.5	-	-	-	-	-	pF
C <sub>PD</sub>	power dissipation capacitance	per buffer; [3] $C_L = 0$ pF; $f = 10$ MHz; $V_{CC} = 5$ V; $V_I = GND$ to $V_{CC}$	-	13.8	-	-	-	-	-	pF

- [1] Typical values are measured at  $T_{amb} = 25$  °C and  $V_{CC} = 2.5$  V, 3.3 V, and 5 V respectively, unless otherwise specified.
- [2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

 $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

 $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in Volts.

Table 8. Noise characteristics

GND = 0 V. For test circuit, see Figure 10.

Symbol	Parameter	Conditions	T	T <sub>amb</sub> = 25 °C			
			Min	Тур	Max		
$V_{CC} = 3.3$	V; C <sub>L</sub> = 50 pF						
V <sub>OL(p)</sub>	LOW-level output voltage (peak)		-	0.3	0.8	V	
$V_{OL(v)}$	LOW-level output voltage (valley)		-0.8	-0.2	-	V	
V <sub>OH(v)</sub>	HIGH-level output voltage (valley)		-	2.9	-	V	
V <sub>IH(AC)</sub>	AC HIGH-level input voltage	dynamic	2.31	-	-	V	
V <sub>IL(AC)</sub>	AC LOW-level input voltage	dynamic	-	-	0.99	V	
$V_{CC} = 5.0$	V; C <sub>L</sub> = 50 pF	<u>'</u>	1				
$V_{OL(p)}$	LOW-level output voltage (peak)		-	0.6	1.5	V	
V <sub>OL(v)</sub>	LOW-level output voltage (valley)		-1.5	-0.6	-	V	
V <sub>OH(v)</sub>	HIGH-level output voltage (valley)		-	4.0	-	V	
V <sub>IH(AC)</sub>	AC HIGH-level input voltage	dynamic	3.5	-	-	V	
V <sub>IL(AC)</sub>	AC LOW-level input voltage	dynamic	-	-	1.5	V	

## 11. Waveforms

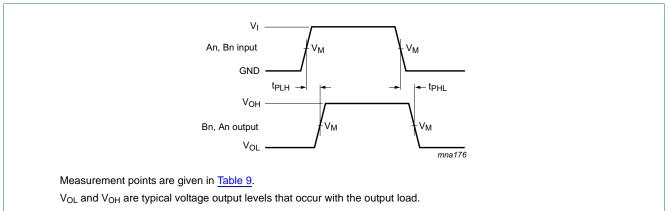


Fig 8. Propagation delay input (An, Bn) to output (Bn, An)

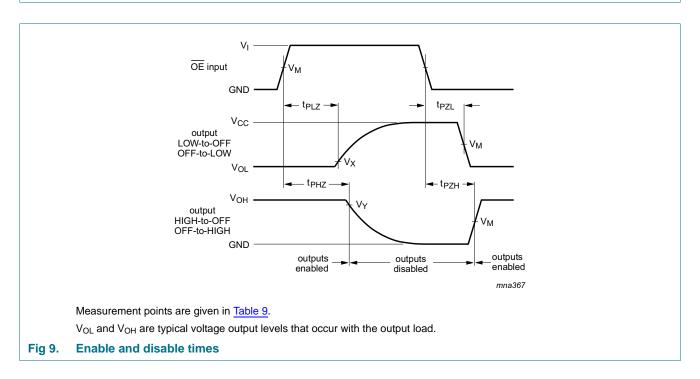
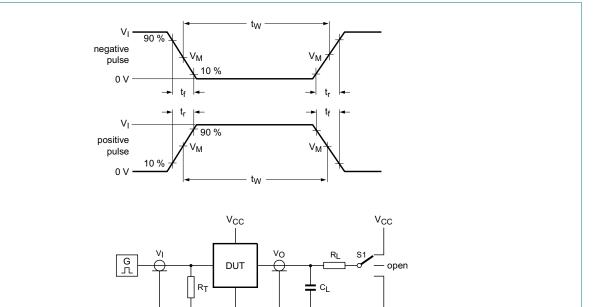


Table 9. Measurement points

Input	Output		
$V_{M}$	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> – 0.3 V

Downloaded from Arrow.com.

10 of 17



001aad983

Test data is given in Table 10.

Definitions test circuit:

 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator

 $C_L$  = Load capacitance including jig and probe capacitance

R<sub>L</sub> = Load resistor

S1 = Test selection switch

Fig 10. Test circuit for measuring switching times

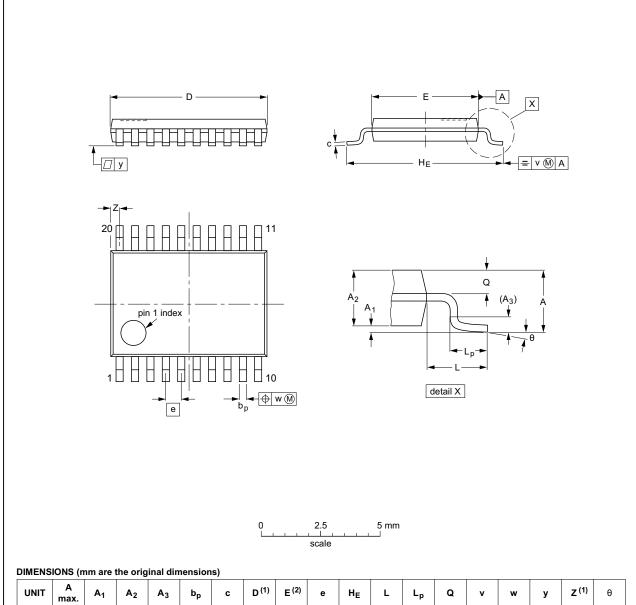
Table 10. Test data

Input		Load		S1 position			
VI	t <sub>r</sub> , t <sub>f</sub>	CL	$R_L$	t <sub>PHL</sub> , t <sub>PLH</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
GND to V <sub>CC</sub>	3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>	

## 12. Package outline

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	<b>A</b> <sub>3</sub>	bp	C	D <sup>(1)</sup>	E (2)	e	HE	L	Lp	Q	>	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

		REFERENCES				
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
	MO-153				<del>99-12-27</del> 03-02-19	
_	IEC				IEC JEDEC JEHA	

Fig 11. Package outline SOT360-1 (TSSOP20)

AHCV245A All information provided in this document is subject to legal disclaimers.

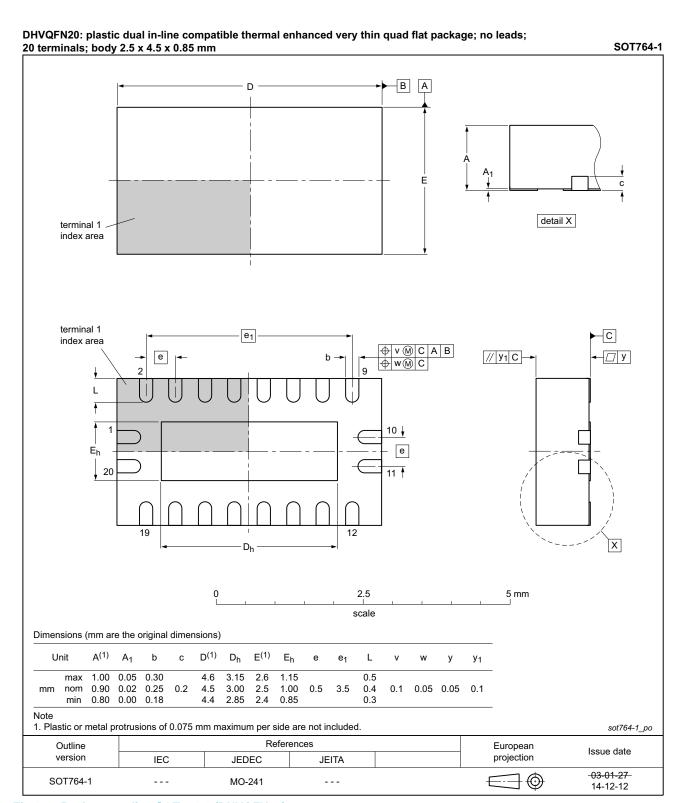


Fig 12. Package outline SOT764-1 (DHVQFN20)

74AHCV245A All information provided in this document is subject to legal disclaimers.

## 13. Abbreviations

#### Table 11. Abbreviations

Acronym	Description	
CDM	Charge Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

# 14. Revision history

## Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHCV245A v.1	20160610	Product data sheet	-	-

14 of 17

## 15. Legal information

#### 15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

#### 15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### 15.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

74AHCV245A

All information provided in this document is subject to legal disclaimers.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond

NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

#### 15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 16. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

# **74AHCV245A**

Octal bus transceiver; 3-state

## 17. Contents

1	General description
2	Features and benefits
3	Ordering information
4	Functional diagram 2
5	Pinning information 3
5.1	Pinning
5.2	Pin description
6	Functional description 4
7	Limiting values4
8	Recommended operating conditions 5
9	Static characteristics 5
9.1	Transfer characteristics waveforms 6
10	Dynamic characteristics
11	Waveforms
12	Package outline
13	Abbreviations14
14	Revision history
15	Legal information
15.1	Data sheet status
15.2	Definitions
15.3	Disclaimers
15.4	Trademarks16
16	Contact information
17	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP Semiconductors N.V. 2016.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 10 June 2016 Document identifier: 74AHCV245A